NSN 5961-01-239-0831

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-239-0831 **Inclosure Material:** Metal **Overall Length:** 1.563 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.614 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 50.0 repetitive peak reverse voltage, peak total value and 1.5 gate trigger voltage, dc **Current Rating Per Characteristic:** 30.00 milliamperes forward current, total rms preset and 50.00 milliamperes forward current, total rms peak and 55.00 amperes source cutoff current horsepower metric **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No